


REMARKS

The above Amendment provides updated continuation information at the top of the specification and also eliminates multiple dependent claims, including improper multiple dependent claims.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

Page 1, the paragraph beginning immediately after the title has been amended as follows:

This is a Rule 1.53(b) Continuation application of Serial No. 09/799,681, filed March 7, 2001, now abandoned, which is a continuation of Serial No. 09/566,740, filed May 9, 2000, now abandoned, which is a continuation of Serial No. 08/951,959, filed October 17, 1997, now abandoned which is a continuation of Serial No. 08/650,905, filed May 17, 1996, now abandoned.

IN THE CLAIMS:

Claims 3 to 7, 9, 13, 14 and 17 have been amended as follows:

3. (Amended) A method as claimed in claim 1 [or 2], wherein said substance liquid at the room temperature under the atmospheric pressure is an organic metal compound.

4. (Amended) A method as claimed in [any one of claims] claim 1 [to 3], wherein said substance liquid at the room temperature under the atmospheric pressure is $\text{Ti}(\text{i} - \text{OC}_3\text{H}_7)_4$.

5. (Amended) A method as claimed in [any one of claims] claim 1 [to 4], wherein said pressurized gas is an inert gas or a reactive gas.

6. (Amended) A method as claimed in [any one of claims] claim 1 [to 5], wherein said nozzle is an expansion-type nozzle.

7. (Amended) A method for forming gas cluster ions, which comprises the step of ionizing the gas cluster formed by the method as claimed in [any one of claims] claim 1 [to 6].

9. (Amended) A method for forming a thin film, which comprises the step of irradiating the cluster ions formed by the method as claimed in claim 7 [or 8] onto a substrate surface, thereby forming a thin film.

13. (Amended) A method for forming a thin film [a] as claimed in claim 11 [or 12], wherein an oxide film is deposited by irradiating cluster ions of a gas containing oxygen and at least an organic metal compound gas onto the substrate surface.

14. (Amended) A method for forming a thin film as claimed in [any one of claims] claim 11 [to 13], which comprises the steps of irradiating oxygen gas cluster ions onto the substrate, and at the same time, or alternately, irradiating a single, or a plurality of, component gas of deposit film onto the substrate surface to cause reaction of the both, thereby depositing a thin ferroelectric film on the substrate surface.

17. (Amended) A method for forming an oxygen-containing gas cluster, which comprises the step of ionizing the gas cluster formed by the method as claimed in claim 15 [or 16].